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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Chen et al.

Serial No.: 09/748,256

Group Art Unit: 2811

Filed: December 27, 2000

Examiner: Ori Nadav

5/12/03

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For: METHOD FOR FABRICATING COMPLEMENTARY METAL OXIDE
SEMICONDUCTOR (CMOS) DEVICES ON A MIXED BULK AND SILICON-ON-
INSULATOR (SOI) SUBSTRATE

Honorable Commissioner of Patents
Washington, D.C. 20231
Box AF

RECEIVED
MAY - 2 2003
TECHNOLOGY CENTER 2800

RESUBMISSION OF AMENDMENT

Sir:

Applicant notes that this Amendment is a Resubmission of the Amendment filed under 37 C. F. R. §1.116 on March 28, 2003. Applicant notes that this Amendment is the same in all respects as the March 28 Amendment, and is filed only, according to the Examiner, because the bottom lines of the March 28 Amendment were not legible in the facsimile transmittal.

In response to the Office Action dated January 28, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the claims to read as follows:

29. (Thrice Amended) A semiconductor device comprising:
- a bulk silicon region comprising single crystal silicon; and
 - a silicon-on-insulator (SOI) region comprising:
 - an insulator layer which is formed beneath an upper portion of said single crystal silicon and has at least one lateral end portion adjacent to a lower portion of said single crystal silicon; and
 - at least one isolation oxide formed in said upper portion of said single crystal

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